

Ultra-fast low gain avalanche diodes for synchrotron X-rays detection



Marco Leite¹
leite@usp.br



Luana Santos Araujo³, Raul Back Campanelli³, Maurício Martins Donatti³, Matheus Gimenez Fernandes³, Gustavo Siqueira Gomes³, Marco Leite¹, Simone Michele Mazza², Jennifer Ott², Rodrigo Estevam De Paula¹, Alan Douglas Pereira³, Jean Marie Polli³, Hartmut Sadrozinski², Guilherme Tomio Saito¹, Bruce Andrew Schumm², Abraham Seiden², Geovane Grossi Araujo de Souza¹, Yuzhan Zhao²



(1) Universidade de São Paulo - USP

(2) Santa Cruz Institute for Particle Physics - UC Santa Cruz

(3) Laboratório Nacional de Luz Síncrotron - CNPq



IHEP/CAS Experimental Physics Department Seminar

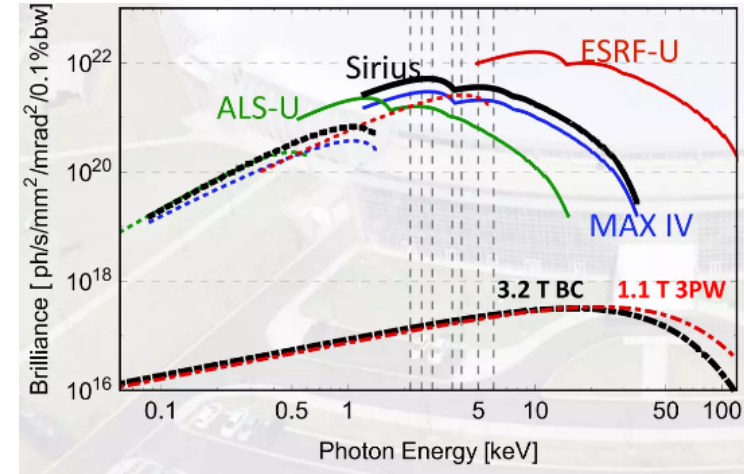
Beijing, Dec. 18th 2025

MINISTÉRIO DA
CIÊNCIA, TECNOLOGIA
E INOVAÇÃO



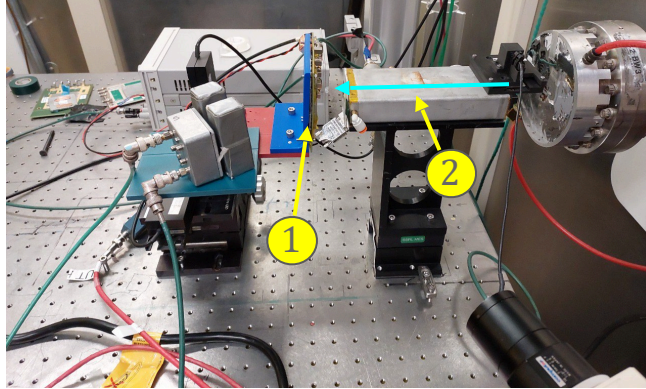
Motivation

- New 4th generation light sources poses many challenges for detectors due to high intensity and fast timing bunch structure (e.g. HEPS, Sirius)
- LGADs are natural sensor candidates to face these challenges :
 - Intrinsic gain \Rightarrow good signal-to-noise ratio \Rightarrow low energy photons
 - Very fast timing \Rightarrow time-resolved applications
 - Radiation hard (TID) \Rightarrow operation at very high intensity beams
 - LHC timing detectors (ATLAS & CMS) \Rightarrow Extensive R&D
- However, synchrotron light application will require :
 - Very fine (few μm) spatial resolution sensors
 - Active region facing the beam
 - Different energy ranges \Rightarrow Sensor thickness optimization



SSRL (SLAC) at Stanford (USA)

Beam Line 11-2 @ SSRL



- ① LGAD setup
- ② Beam direction

Beam Line Specifications

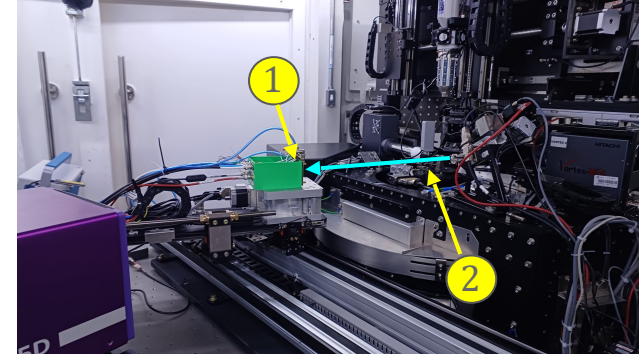
Source

26-pole, 2.0-Tesla Wiggler, ≤ 1.5 mrad variable acceptance

	Energy Range	Resolution $\Delta E/E$	Spot Size
Focused	5000-20000 eV	1×10^{-4}	$0.5 \times 1 \text{ mm}^2$
Unfocused	5000-37000 eV	1×10^{-4}	$3 \times 30 \text{ mm}^2$
Collimated	5000-23000 eV	1×10^{-4}	$2 \times 30 \text{ mm}^2$

Sirius at LNSL-CNPEM in São Paulo (Brazil)

Carnaúba beam line @ Sirius



PARAMETERS

Parameter	Value	Condition
Energy Range *	2.05 – 15 keV	Si(111)
Energy Resolution ($\Delta E/E$)	$10^{-4} - 10^{-5}$	
Harmonic Content	$< 10^{-5}$	Above 5 keV
Energy Scan	Yes	
Beam size at sample [μm] @Tarumã	$0.15 \times 0.15 (0.55 \times 0.55)$	8 keV (2 keV)
Beam Divergence at sample [mrad] @Tarumã	(1 x 1)	All energy range
Estimated flux [ph/s/100 mA] @Tarumã	10^{11}	–

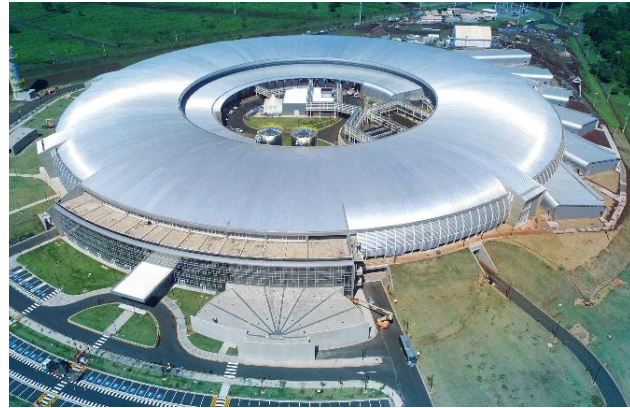
* BL being commissioned, available now : 5.8 to 13.8 keV.

Both sites provide high intensity, quasi-monochromatic pulsed X-ray beams (10 ps wide pulses, 2 ns apart) with several geometries

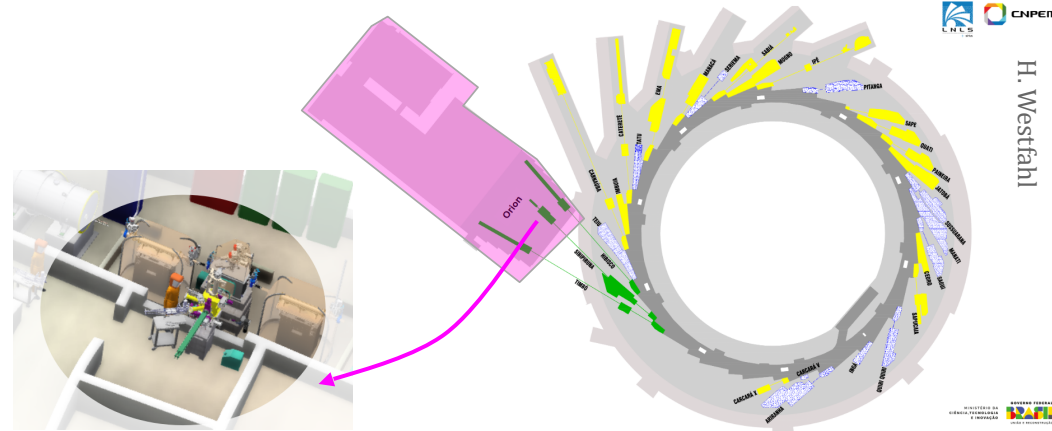
The Sirius Light Source in São Paulo (Brazil)

Orion Project at Sirius ([link](#))

- 3 new beam lines for soft, tender and hard x-Rays
- Installed in a Level 4 biosecurity laboratory
- State-of-the-art facility for highly contagious pathogens research
- New generation of detectors (and sensors) are needed for high frame rate/ high resolution imaging of biological samples

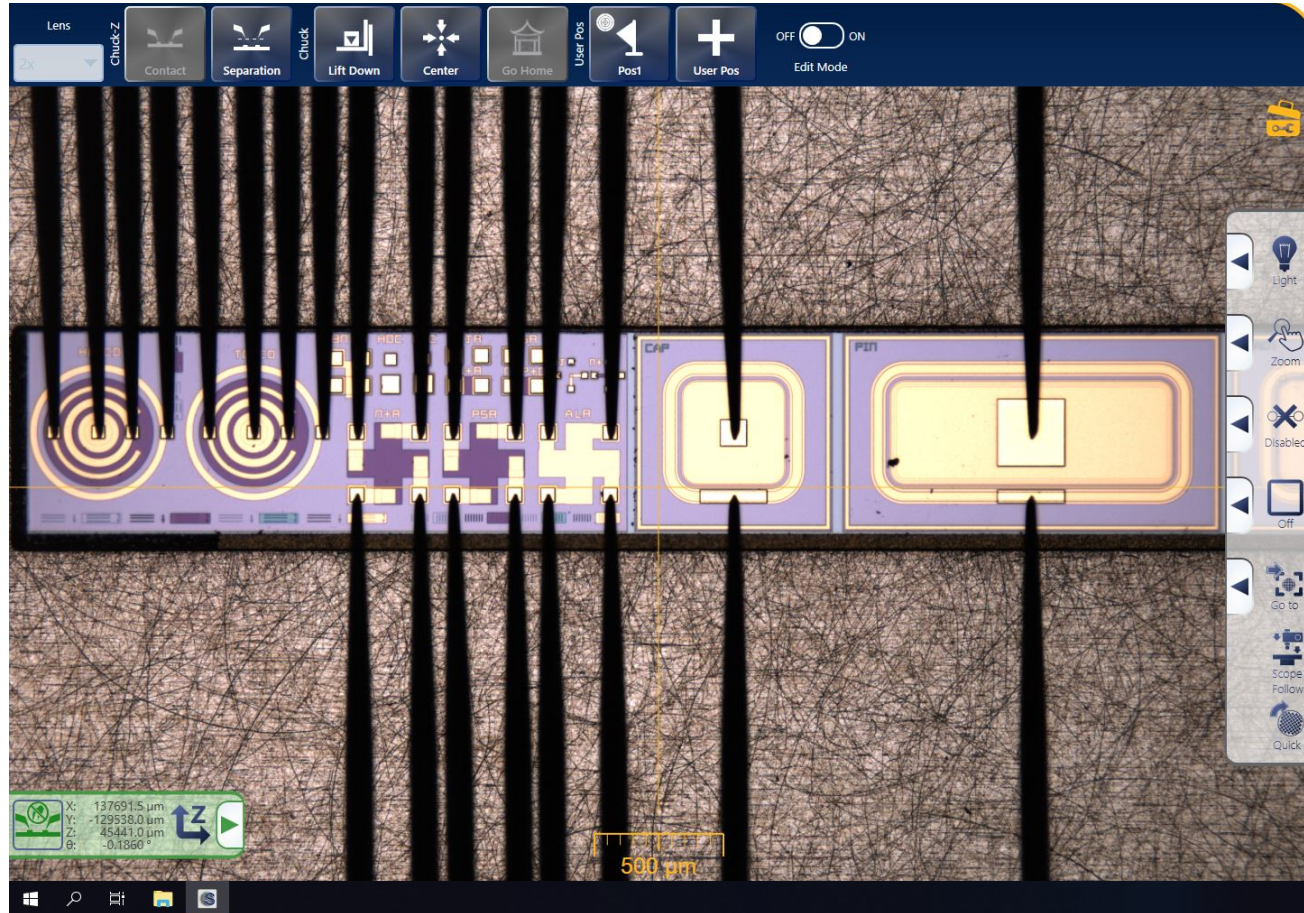


- 4th generation light source (National Laboratory [link](#))
- 27 beamlines (2019 - 2028)
- Phase I (200mA) :
 - 10 operational beam lines, 2 commissioning , 2 construction
- Fase II (350mA) :
 - 1 in construction, 9 in project
- Increasing demand for faster X-ray detectors for imaging and non-imaging applications.



High intensity, quasi-monochromatic focused pulsed X-ray beams (10 ps wide pulses, 2 ns apart)

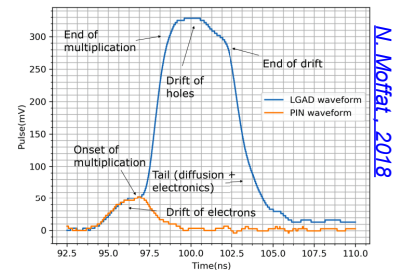
Low Gain Avalanche Diodes



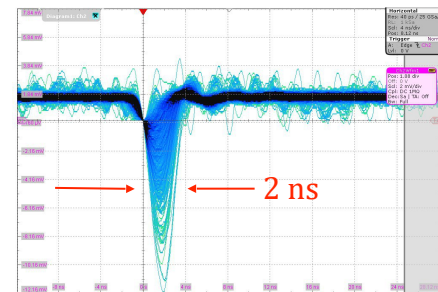
IHEP-IME LGAD test structure for ATLAS HGTD being probed at the USP semiconductor sensor lab.

Low Gain Avalanche Diodes (LGAD)

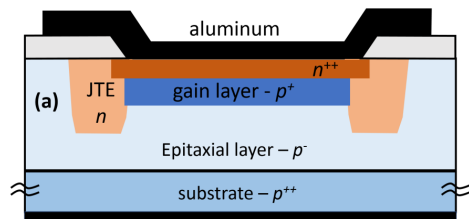
- Proposal made by the RD50 collaboration ([Sadrozinski et al](#)) ~ 2013 aiming at very radiation hard devices for LHC etc.
- LGADs are PiN Si diodes + an intrinsic gain layer for charge multiplication
 - Moderate gain (10 ~ 50) \Rightarrow low energy X-rays
 - Very fast response (< 30 ps for MIP) \Rightarrow time resolved applications
 - Devices can be fabricated from ~30 μm to ~300 μm active thickness



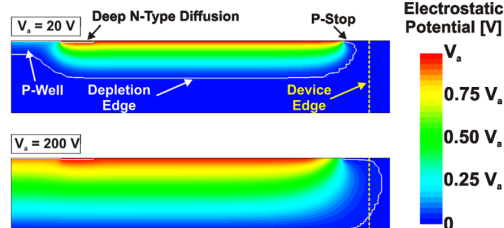
LGAD response to ^{90}Sr electrons



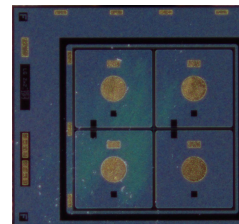
LGAD structure



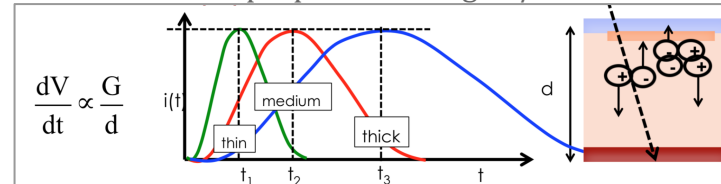
LGAD Internal Electrical Field



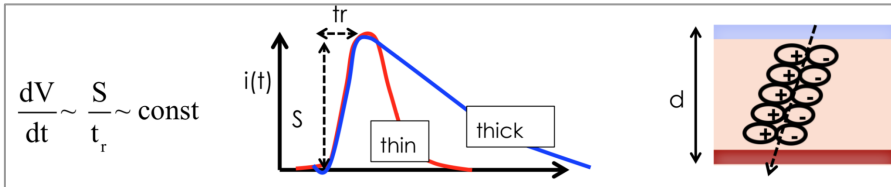
2x2 LGAD (HPK)



LGAD: rise time proportional to gain/thickness



Planar detector: fixed rise time

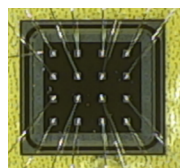
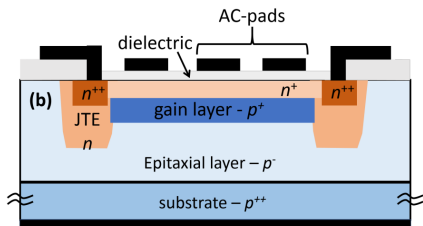


LGAD Design Variations

Fact: DC-LGADs (e.g from ATLAS and CMS) have a coarse spatial resolution and large inter pad (inactive) region ($\sim 50 \mu\text{m}$ to $100 \mu\text{m}$)

Challenge: How to fabricate devices with optimal spatial resolution (μm) and small upstream dead-region?

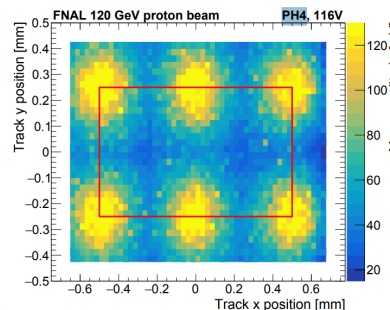
AC-LGAD ([link](#), [link](#))



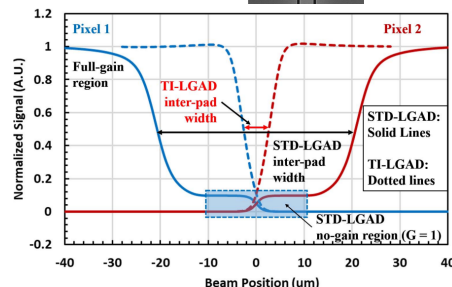
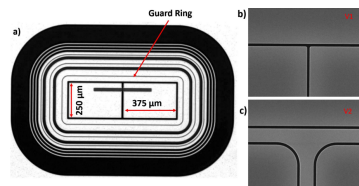
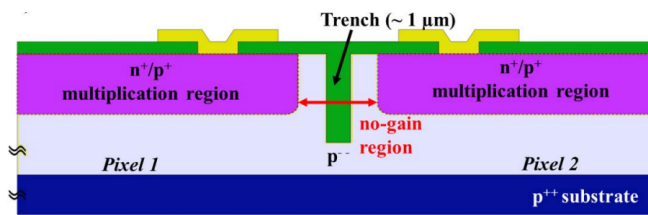
HPK AC-LGAD
150 μm ;
500 μm

$$\sigma_t \approx 21 \text{ ps}$$

$$\sigma_s \approx 41 \mu\text{m}$$

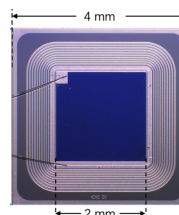
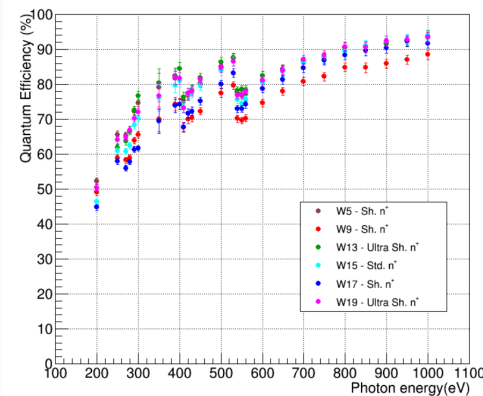
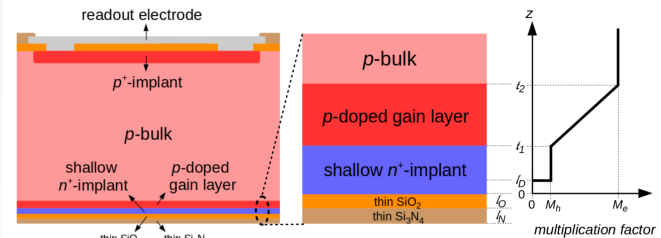


Trench Isolated (TI-LGAD) ([link](#))




TCAD
simulation:
IP $\sim 5 \mu\text{m}$

Inverted LGAD ([link](#))



X-rays down
to 200eV

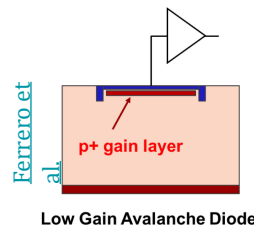


Characterizing the performance of Low Gain Avalanche Diodes using synchrotron radiation

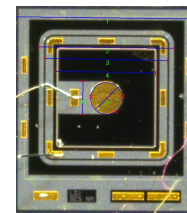
I - Single Pad LGADs tests @ SSRL BL 11-2

<https://iopscience.iop.org/article/10.1088/1748-0221/18/10/P10006>

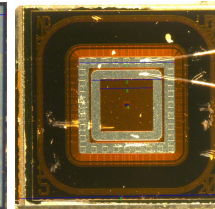
- "Flat" beam : 25mm x 1 mm (nominal)
- Energy scan from 5 to 37 keV (70 keV with harmonics)
- Bias Scan
- Single pad (1.3 x 1.3 mm²) LGADs



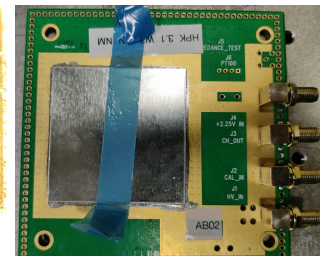
Low Gain Avalanche Diode



HPK
DC LGAD



BNL
DC LGAD



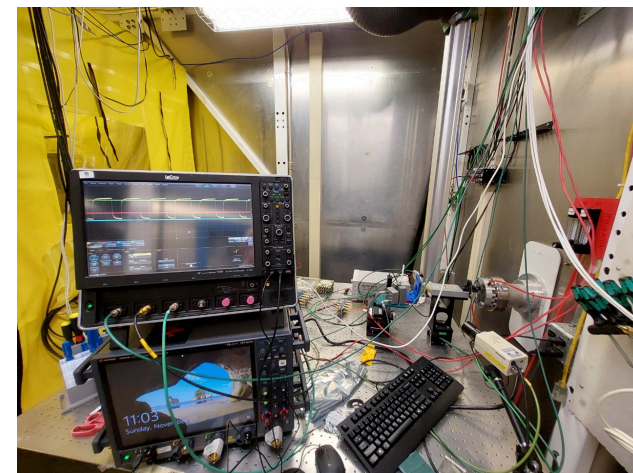
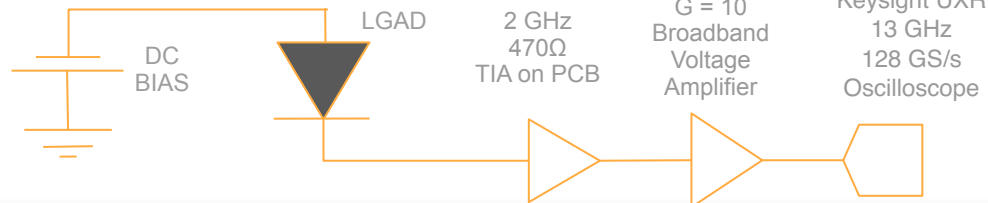
Santa Cruz board with
LGAD and 1-ch. amplifier

Devices Tested

Device	Active Thick.	Gain Layer	Breakdown
HPK LGAD type 3.1	50 μm	shallow (1 μm)	$\sim 230\text{ V}$
HPK LGAD type 3.2	50 μm	deep (2 μm)	$\sim 130\text{ V}$
HPK PIN	50 μm	no gain layer	$\sim 400\text{ V}$
BNL LGAD 20 μm	20 μm	shallow (1 μm)	$\sim 100\text{ V}$


For details,
See [Ref.](#)

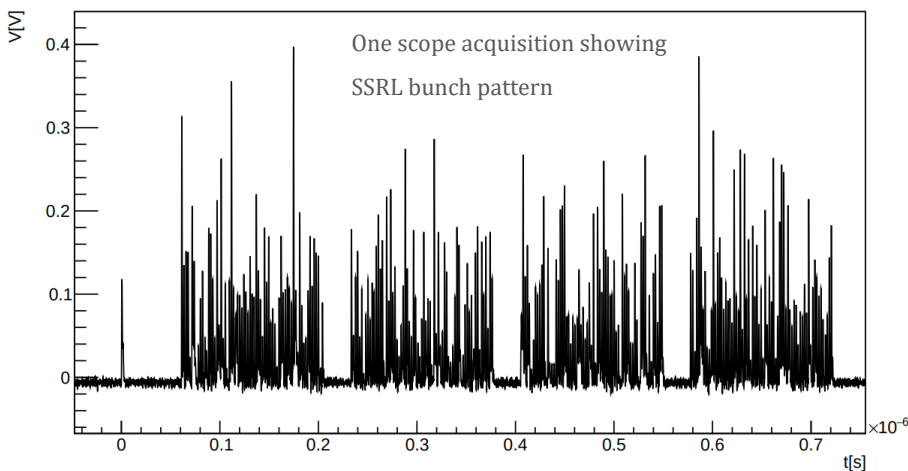
Simple
Measurement
Setup



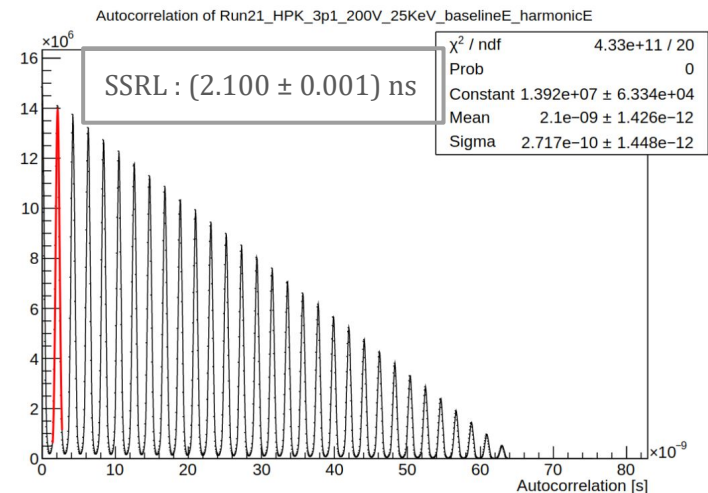
Signal processing - I : How to measure timing ?

- For MIP, we use a telescope for timing measurement (Δt) ; for X-rays we have to resort to something else
- We can rely on the very uniform bunch separation of 2.1 ns
- This can be measured using the LGAD !
- The SSRL fill structure is : ...1-0-fill-0-fill-0-fill-0-fill-0...

SSRL News	Photon Source Parameters
User Resources	Beam Line Map Beam Lines by Techniques Beam Lines by Number
Beam Lines	
Science at SSRL	
Publications	
SPEAR3	
Safety	
Staff Resources	
Contact Us	
 U.S. DEPARTMENT OF ENERGY Office of Science	
Beam Energy	3 GeV
Injection Energy	3 GeV
Current	500 mA
Fill Pattern	280 bunches distributed in 4 groups of 70 bunches each
Circumference	234.137
Radio Frequency	476.315 MHz
Bunch Spacing	2.1 n
Horizontal Emittance	10 nm ² /rad
Vertical Emittance	14 pm ² /rad
Critical Energy	7.6 keV
Energy Spread	0.097

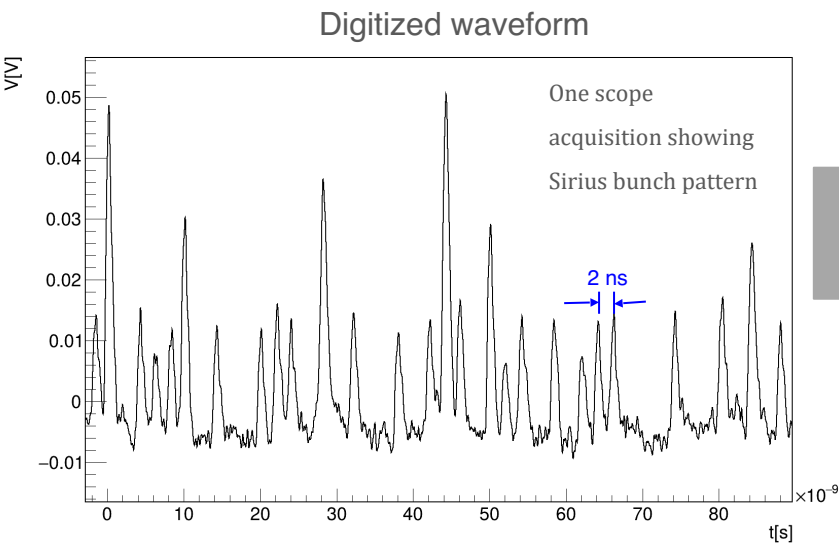


Many

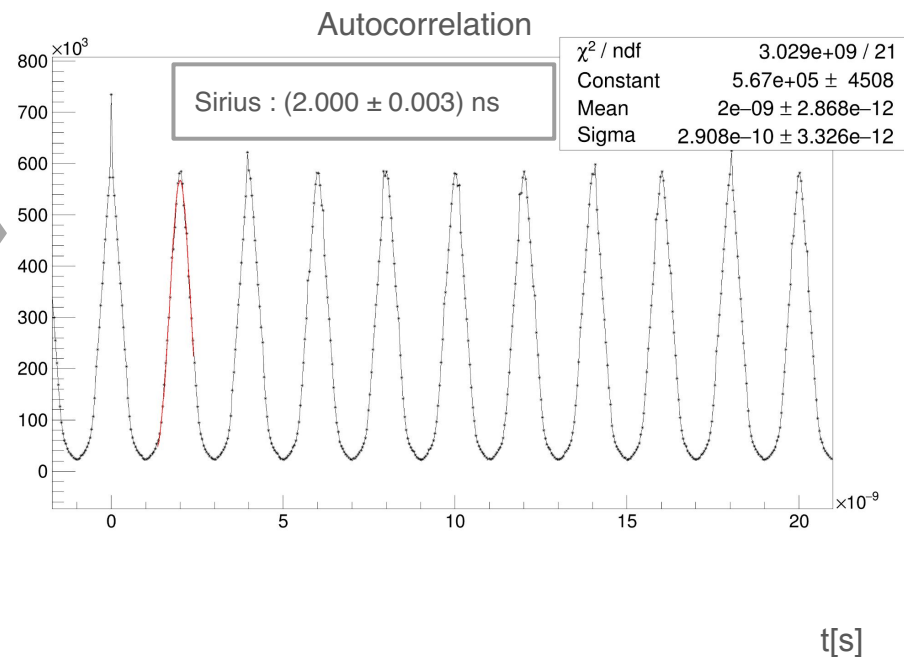


Signal processing - I : How to measure timing ?

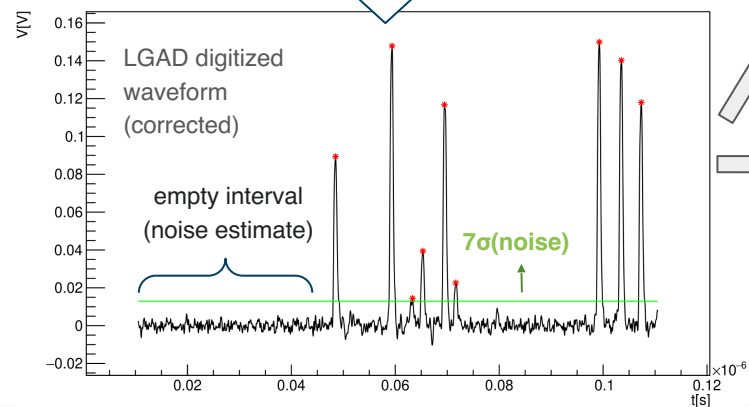
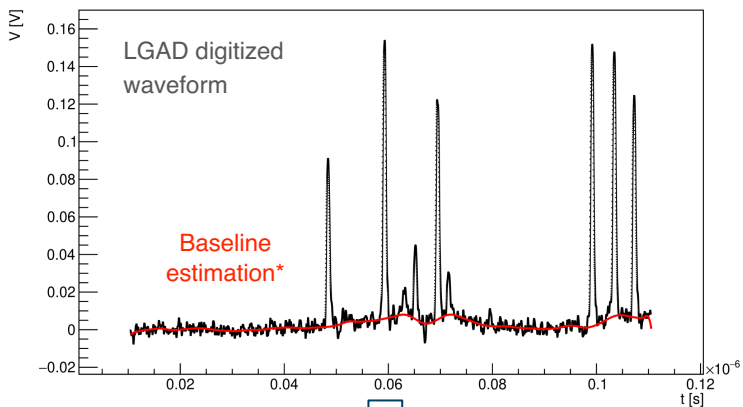
- For Sirius, every bunch in the orbit is filled (2 ns separation)



Many

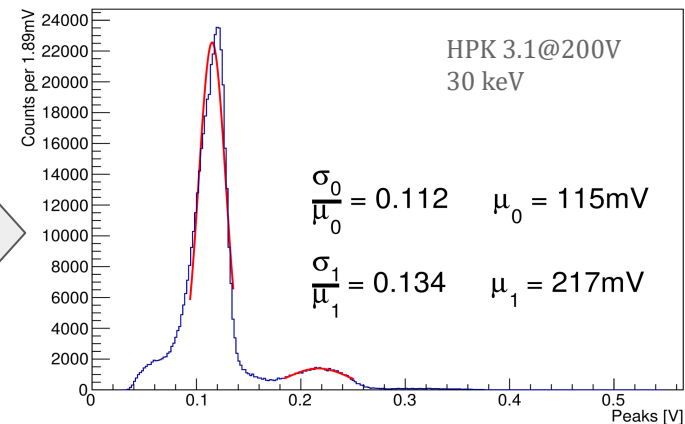


- All data from oscilloscope digitized waveforms



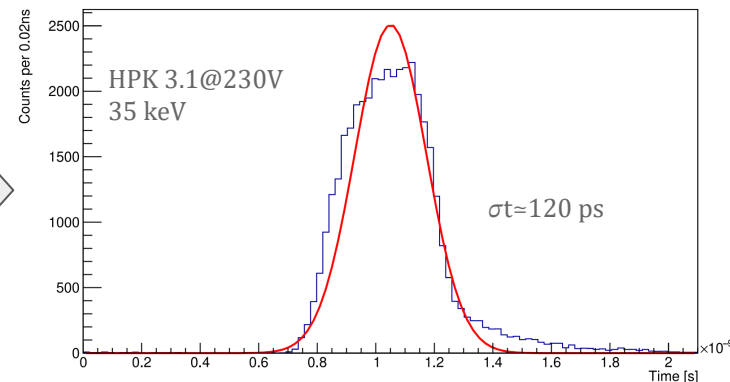
Energy

$\sigma E/E$ from Amplitude distribution



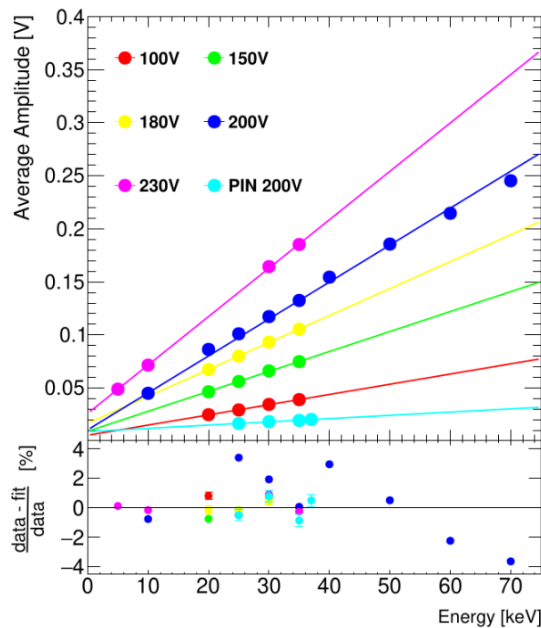
Timing

σt based on 2.1 ns interval (20% CFD)

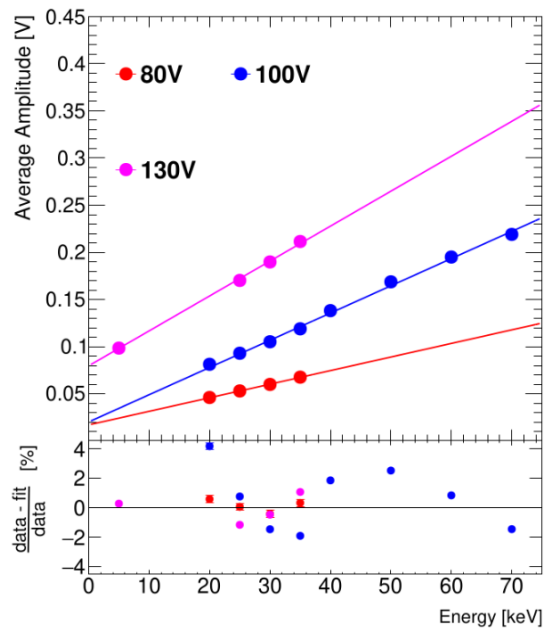


*asymmetric reweighted penalized least squares smoothing

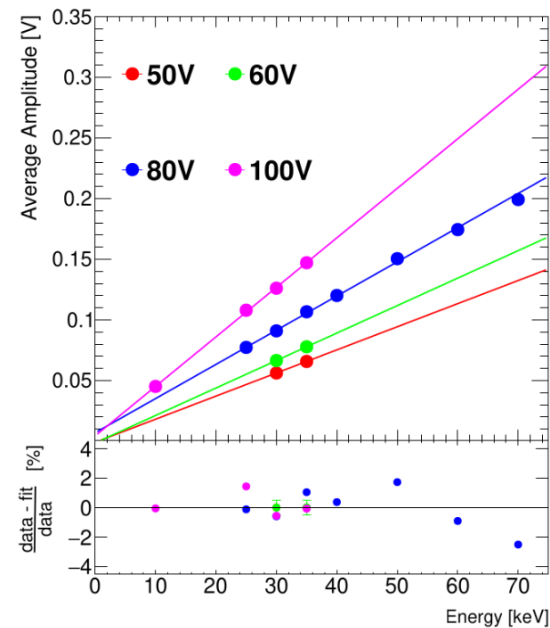
Linearity of response



(a) HPK PIN and type 3.1 LGAD

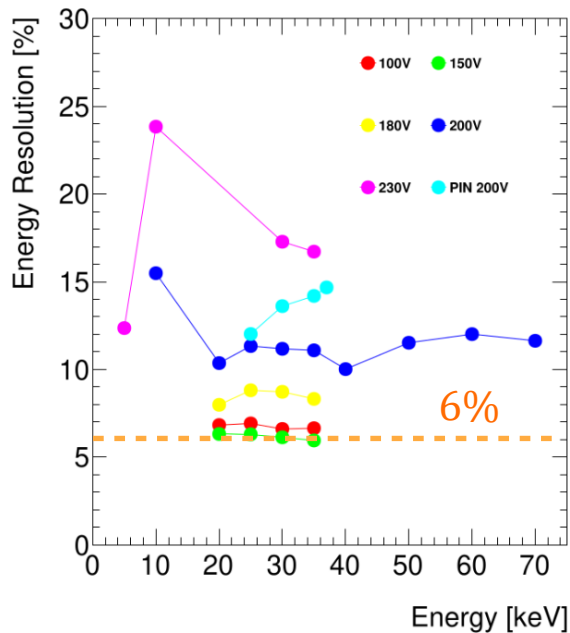


(b) HPK type 3.2 LGAD

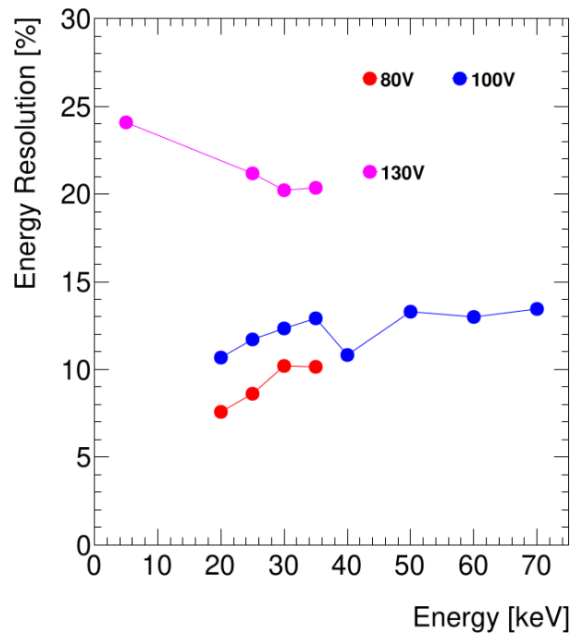


(c) BNL 20um LGAD

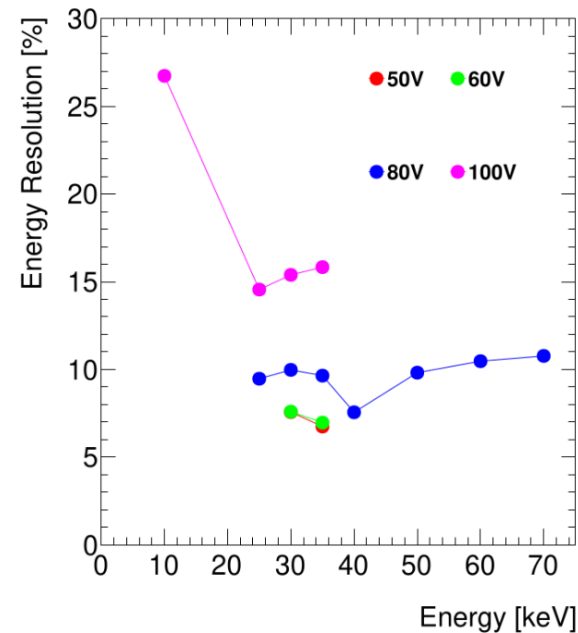
Energy resolution



(a) HPK PIN and type 3.1 LGAD

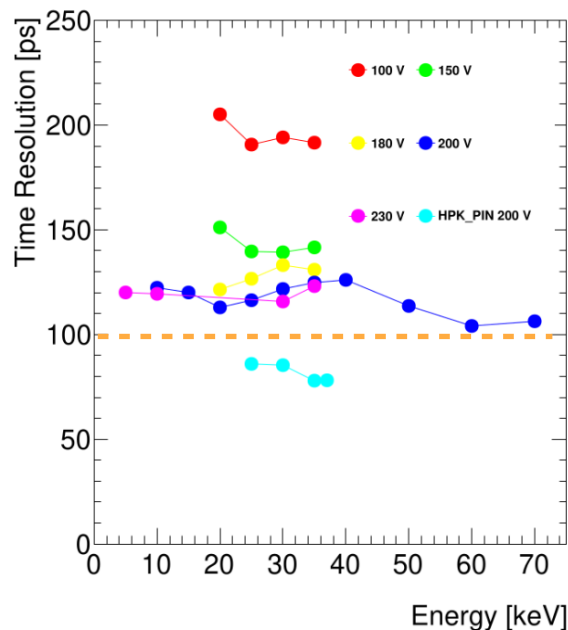


(b) HPK type 3.2 LGAD

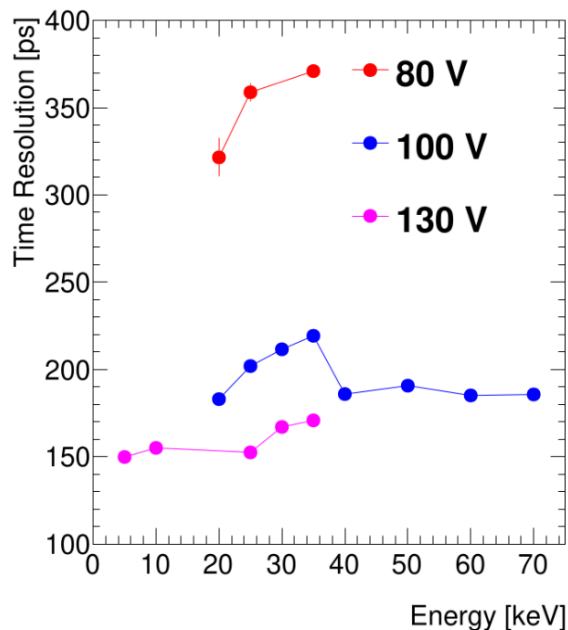


(c) BNL 20um LGAD

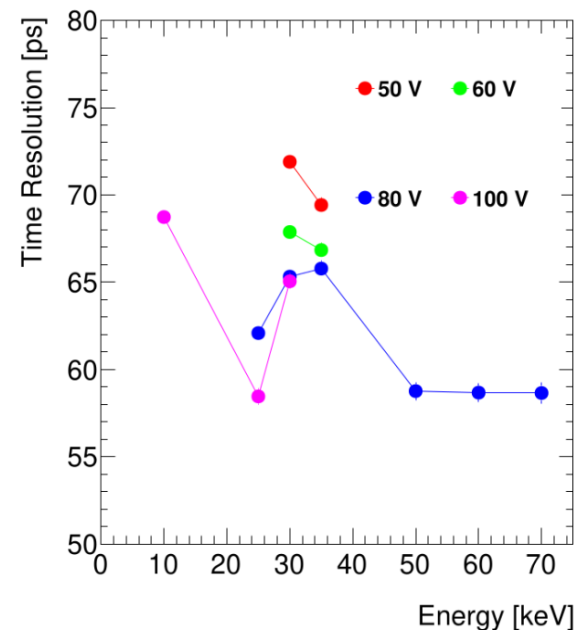
Time resolution



(a) HPK PIN and type 3.1 LGAD



(b) HPK type 3.2 LGAD



(c) BNL 20um LGAD

Best energy
resolution

Best time
resolution

	HPK PIN	HPK3.1		HPK3.2		BNL 20um	
Bias V	200 V	150 V	230 V	80 V	130 V	50 V	100 V
Energy Resolution	14 %	6 %	17 %	10 %	20 %	6 %	16 %
Energy Response	19 mV	75 mV	185 mV	68 mV	211 mV	66 mV	147 mV
σ_t CFD	78 ps	141 ps	123 ps	371 ps	171 ps	69 ps	65 ps

Table 2: Summary of energy and time resolution for the three tested sensors for the different bias voltages that yield the best energy and best time resolution for a 35 keV X-ray beam energy.

The Carnaúba Beam Line

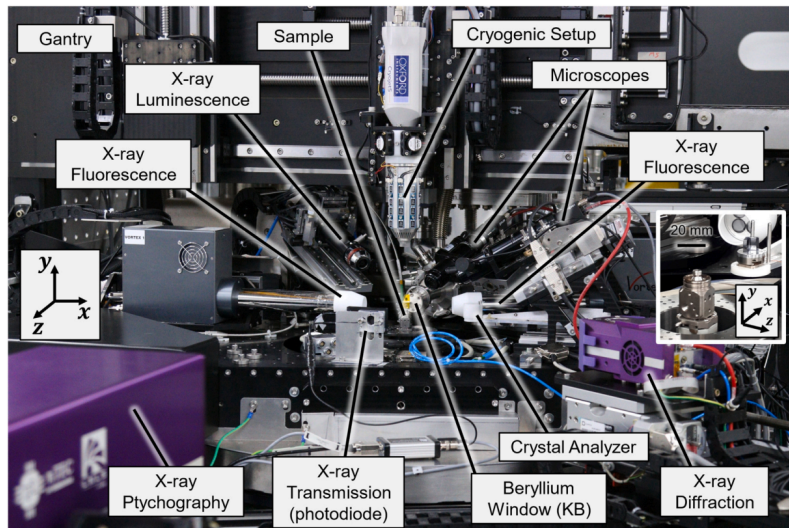
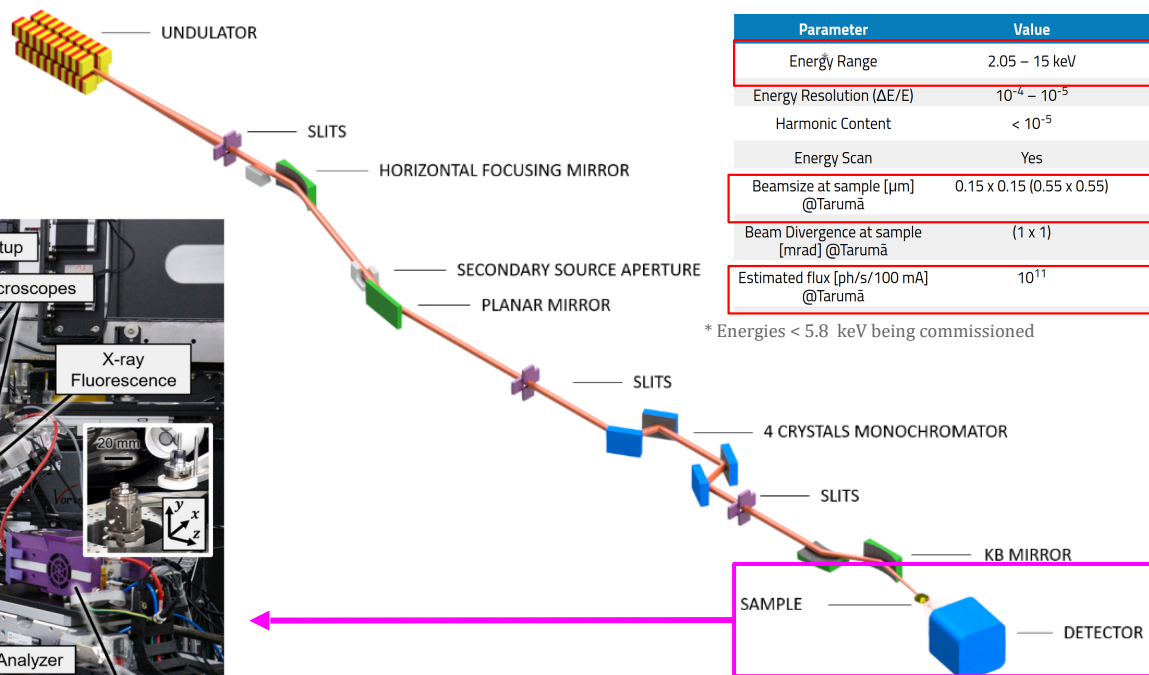
- One of the 10 operational beam lines
- Fully instrumented
- 2.1 to 15 keV X-rays
- Beam size from 150 nm to 350 μm

[link](#), [Tolentino 2023](#)

PARAMETERS

Parameter	Value	Condition
Energy Range	2.05 – 15 keV	Si(111)
Energy Resolution ($\Delta E/E$)	10^{-4} – 10^{-5}	
Harmonic Content	$< 10^{-5}$	Above 5 keV
Energy Scan	Yes	
Beamsize at sample [μm] @Tarumã	0.15 x 0.15 (0.55 x 0.55)	8 keV (2 keV)
Beam Divergence at sample [mrad] @Tarumã	(1 x 1)	All energy range
Estimated flux [ph/s/100 mA] @Tarumã	10^{11}	–

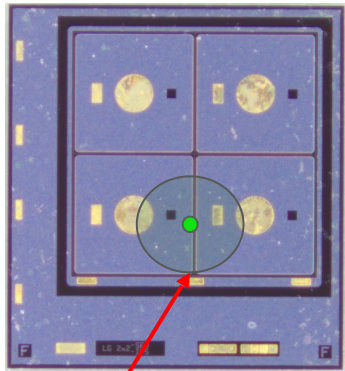
* Energies < 5.8 keV being commissioned



High intensity, quasi-monochromatic focused pulsed X-ray beams (10 ps wide pulses, 2 ns apart)

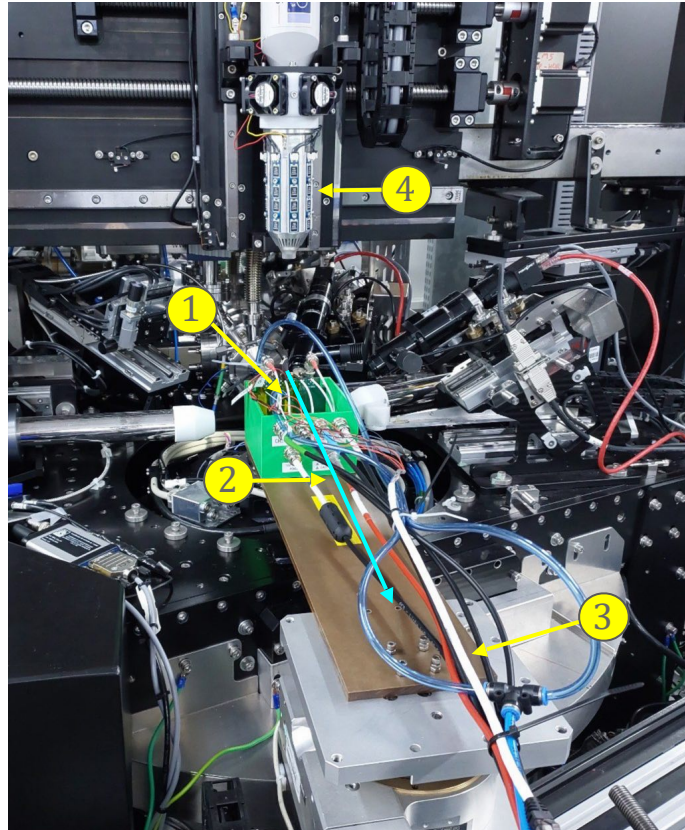
2x2 LGADs (HPK 3.1) tests @ Sirius Carnaúba beamline

- ATLAS HGTD HPK 3.1 2x2 array prototype
- $50\text{ }\mu\text{m}$ active thickness , IP $70\text{ }\mu\text{m}$
- gain : 12 (150 V) ~ 32 (230 V)
- Detector can move and rotate wrt to the beam
- LN2 nozzle can be used to cool down the DUT
- Energy/timing resolution wrt :
 - X-ray energy, bias and temperature
- Interface to EPICS from machine to access experimental conditions (beam intensity, linear stage position, shutters etc.)



2x2 HPK 3.1
LGAD array

$350\text{ }\mu\text{m}$ or 150 nm X-ray beam

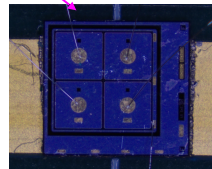
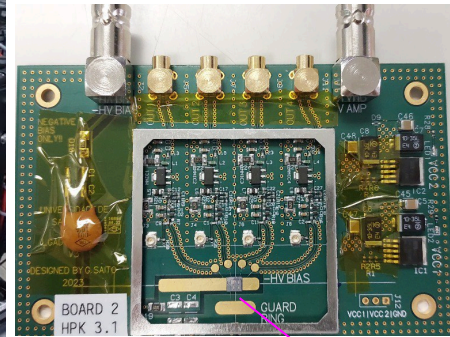
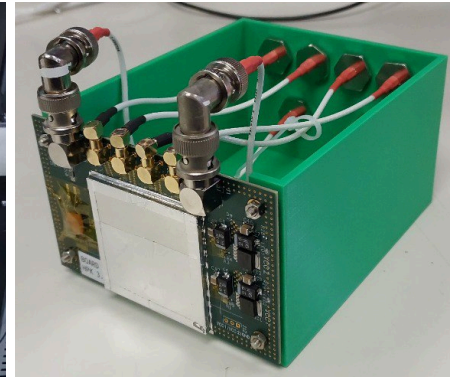


① LGAD

② Beam direction

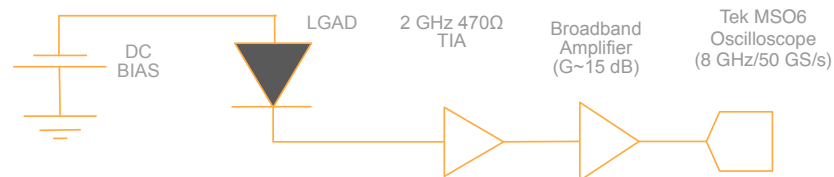
③ Linear stage

④ Cooling nozzle

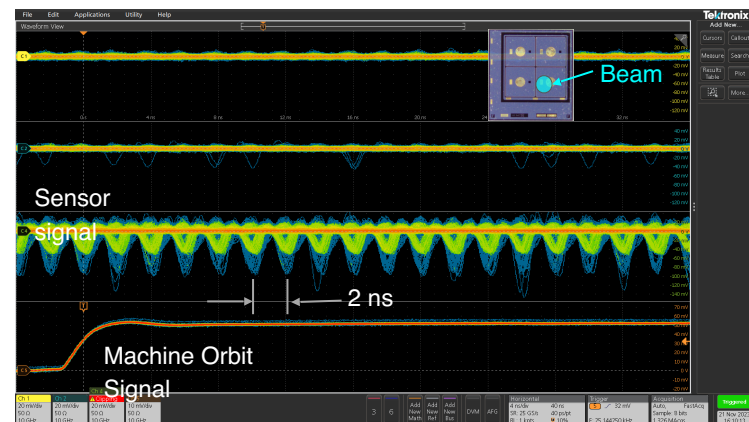
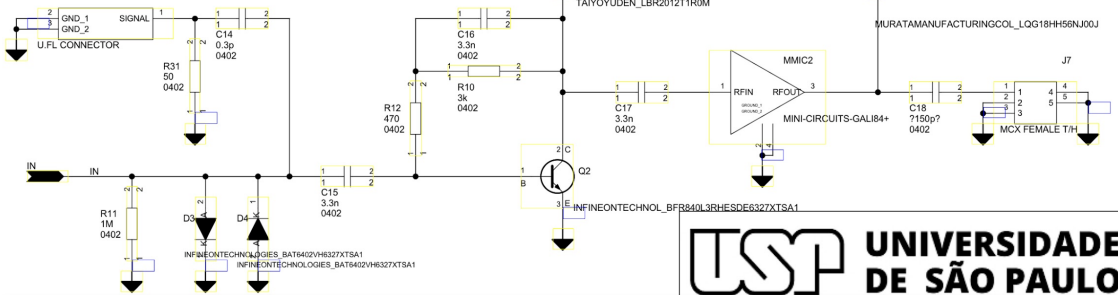
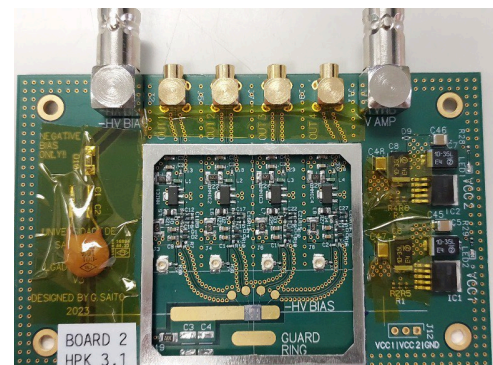


Signal processing and data acquisition

- 4 channel 2-stage amplifier board
- Signal (charge) injection
- Jitter from electronics < 1 ps
- Onboard voltage regulators
- Data acquisition : 8GHz, 50GS/s Oscilloscope \Rightarrow store digitized waveforms

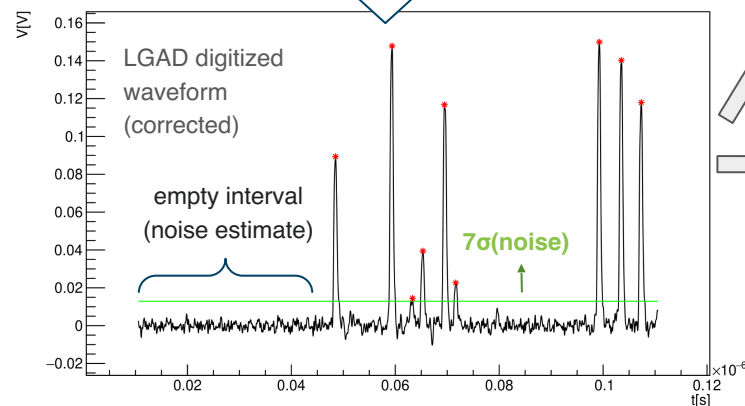
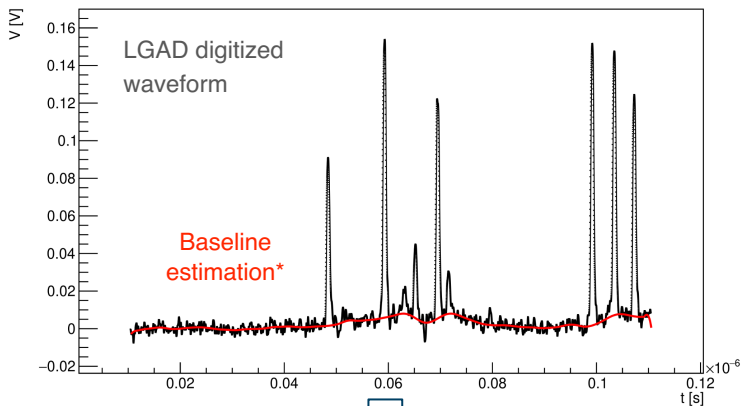


UC St. Cruz 1st stage amplifier + broadband amplifier (MMIC Gali84+)



Signal processing II : baseline correction

- Digitized signal has significant baseline shift \Rightarrow correct offline



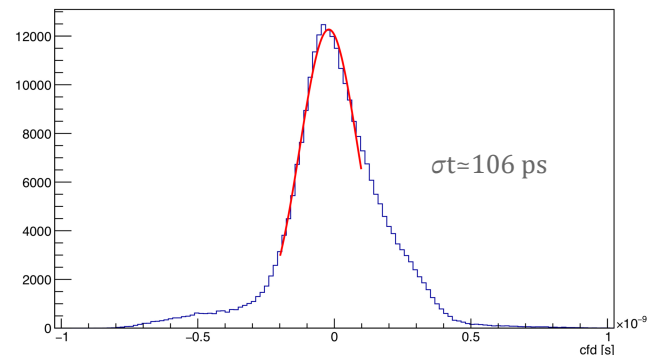
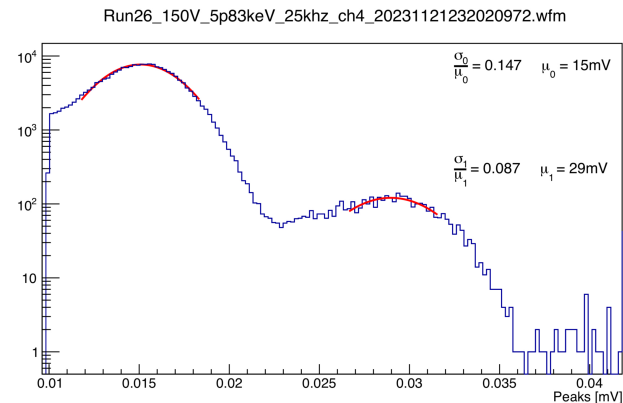
Energy

$\sigma E/E$ from
Amplitude
distribution

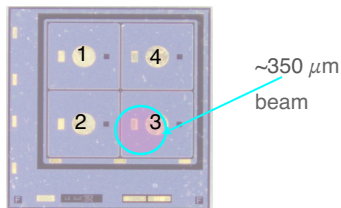
Timing

σ_t based on
2 ns bunch
interval
(20% CFD)

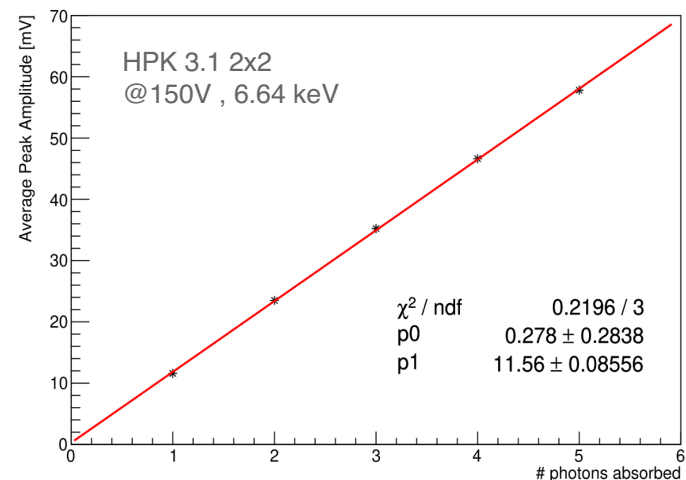
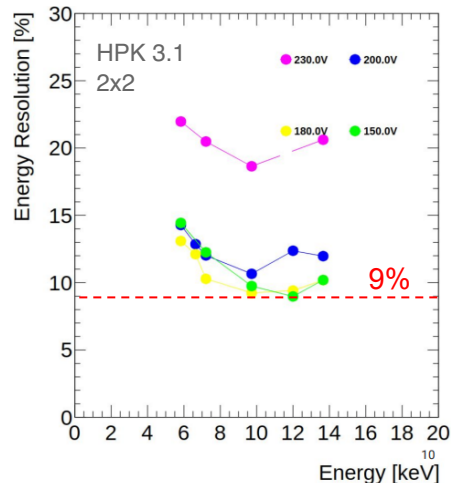
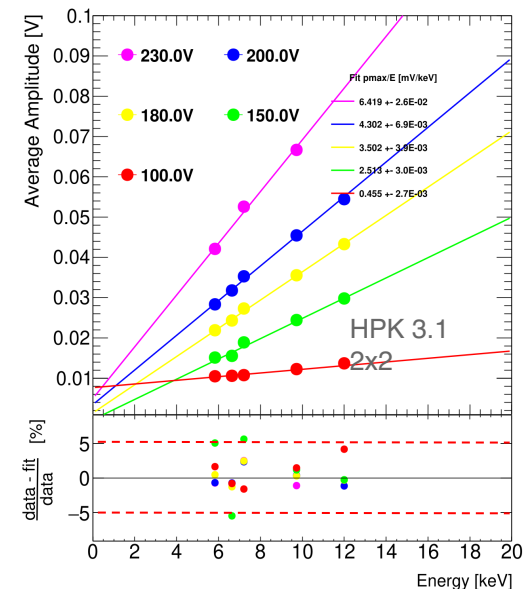
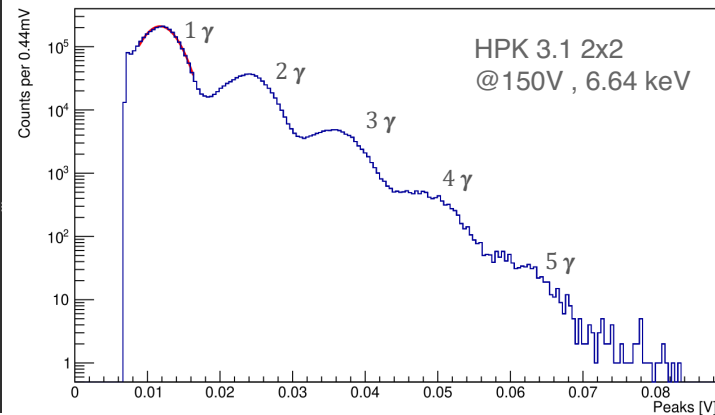
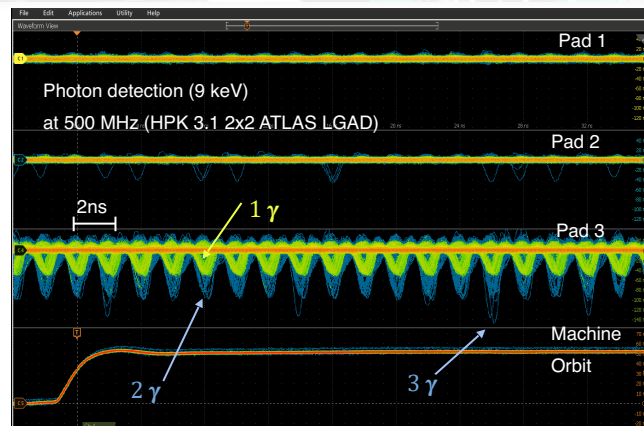
*asymmetric reweighted penalized least squares smoothing



2x2 LGADs (HPK 3.1) Energy response

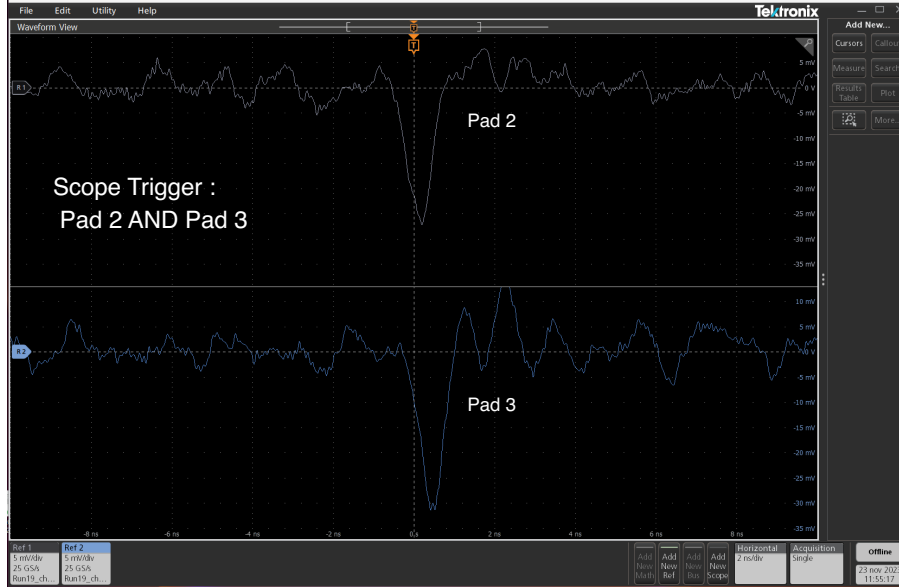
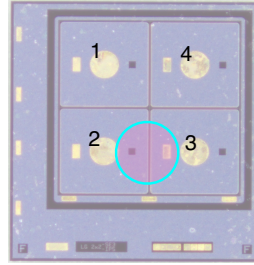


~350 μm
beam

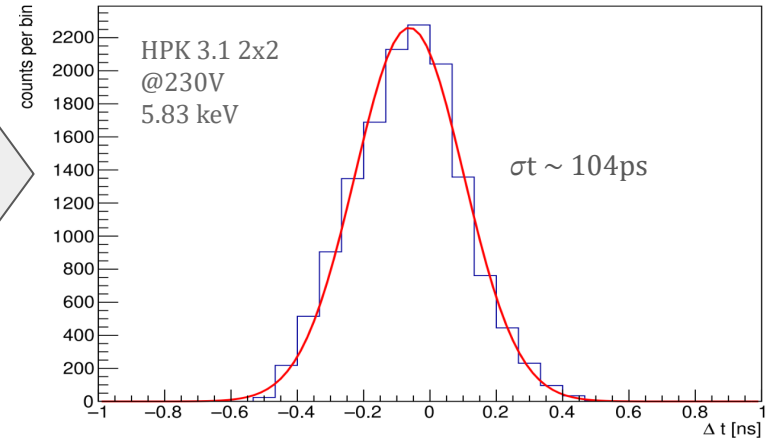


An alternative way to measure timing

- Multiple photon conversions can be used to measure the intrinsic timing resolution
 - $\sigma(t_2 - t_3)$
- Data was taken with AND between two pads signals



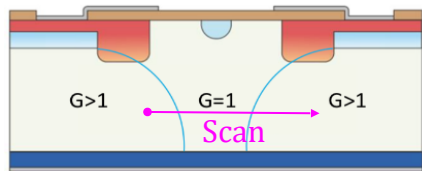
CFD
(20%)



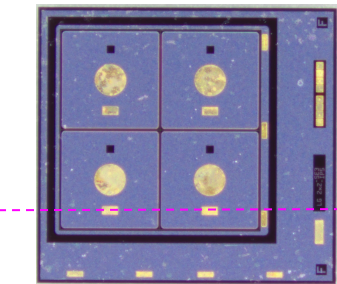
Gain and interpad measurements

Skomina et al

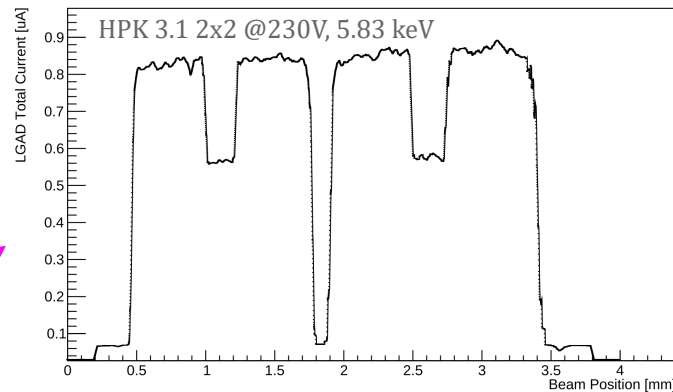
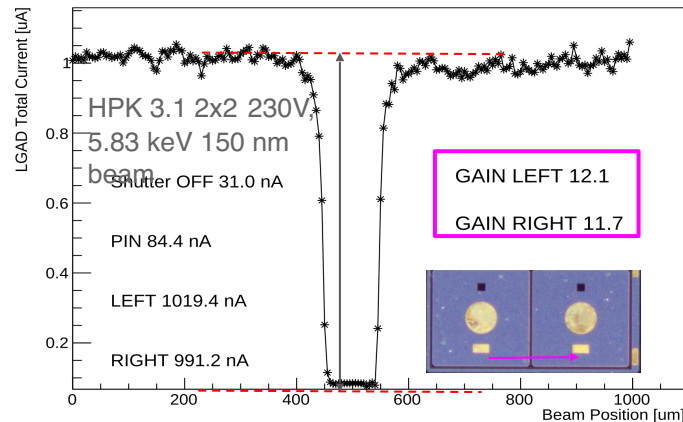
- Use a focused 150 nm beam
- 5 μm step lateral scan between 2 pads



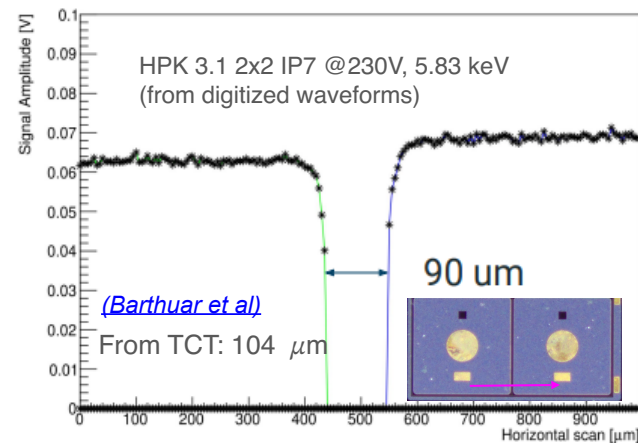
- Extract device gain and from ratio $(G>1) / (G=1)$ by current or pulse amplitude
- Also interpad distance



LGAD CURRENT profile



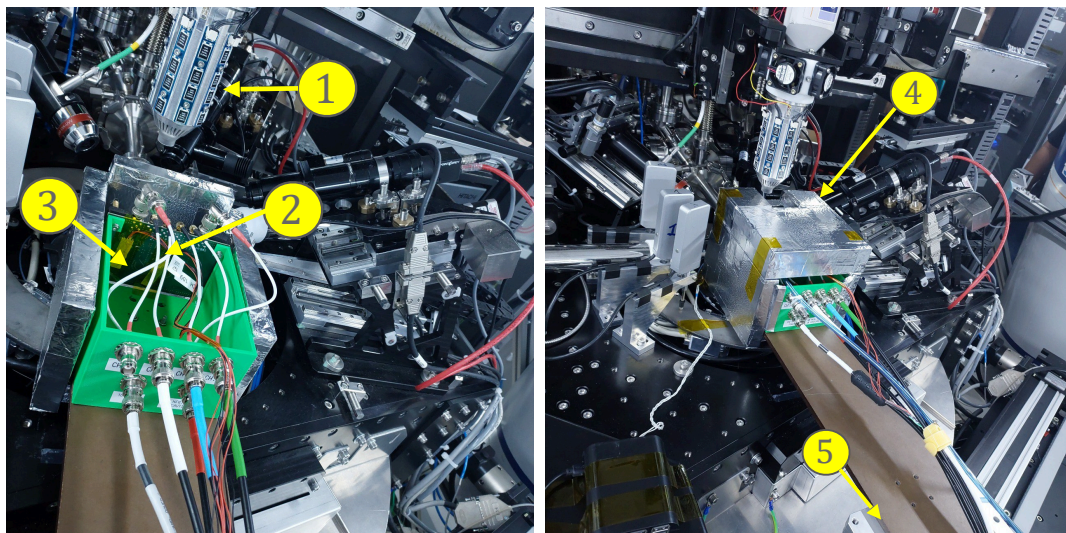
LGAD PULSE AMPLITUDE profile



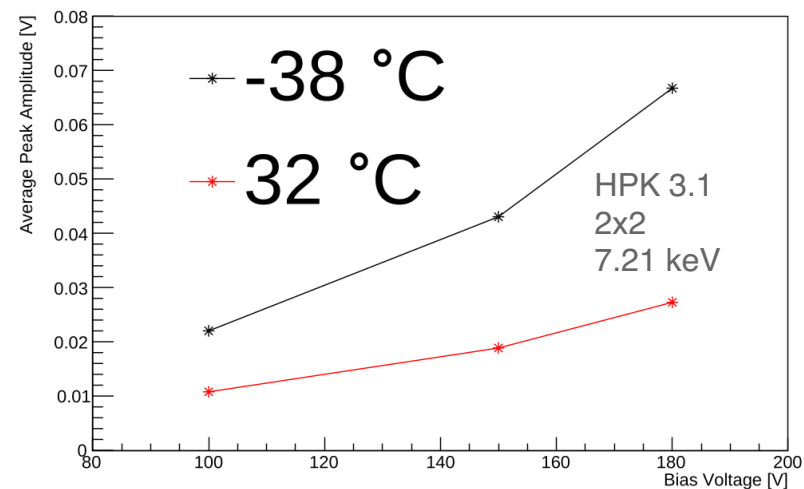
Temperature response

- HPK 3.1 2x2 array
- N2 cooling nozzle and detector position remotely controlled
- Temperature recorded by 2 PT100 on the PCB

- Beam line using a focused beam at 7.21 keV
- Bias and temperature scan
- Gain increases as temperature decreases
 - as expected ([W. Sun et al](#))

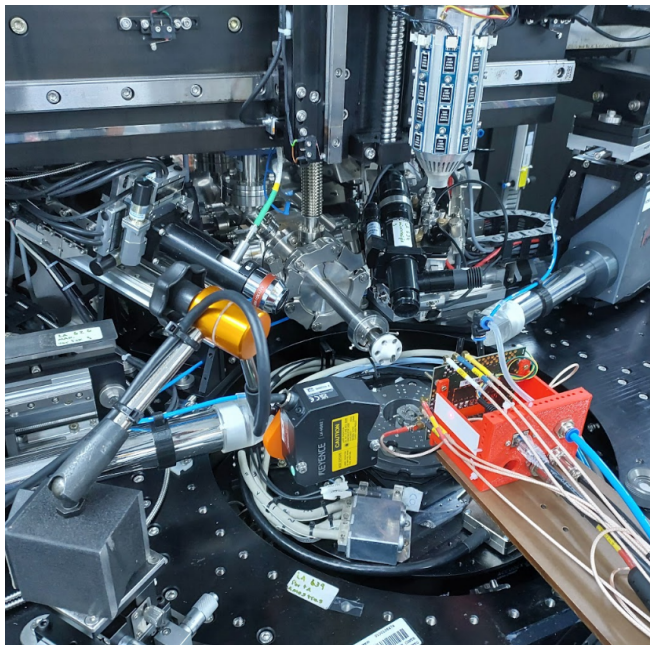


① N2 Nozzle ② LGAD ③ PT100 ④ Insulation box ⑤ Linear stage



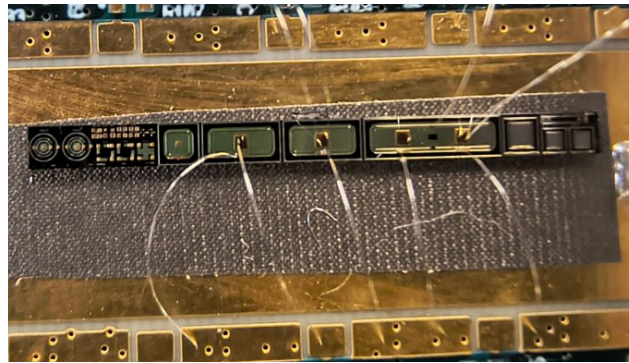
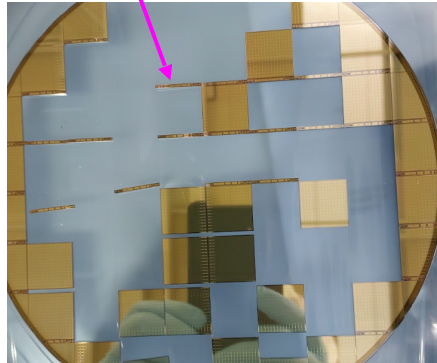
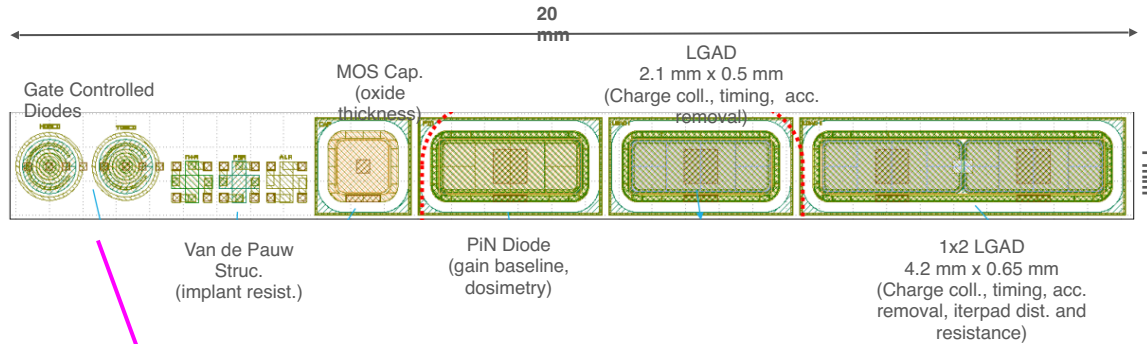
IHEP-IME and FBK TI-LGAD recent tests @ Sirius

PRELIMINARY

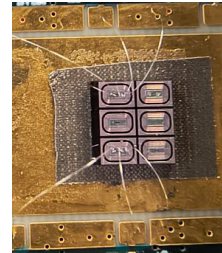
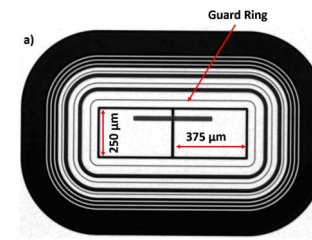
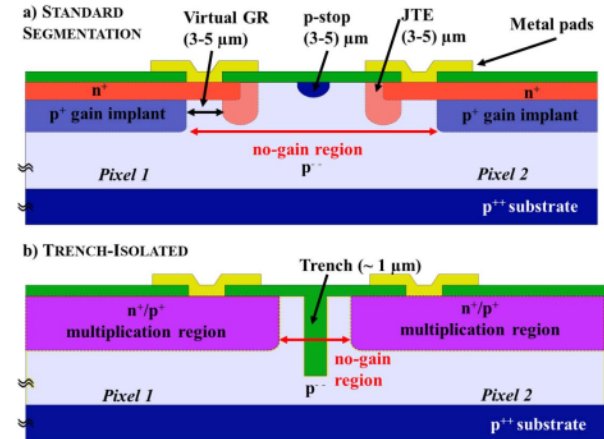


IHEP-IME and FBK TI-LGAD recent tests @ Sirius

- ATLAS HGTD IHEP-IME QA/QC test structure with carbon-enriched "standard" DC-LGADs
- 50 μm active thickness , gain ~ 30 @150V



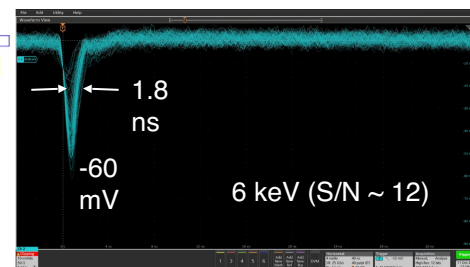
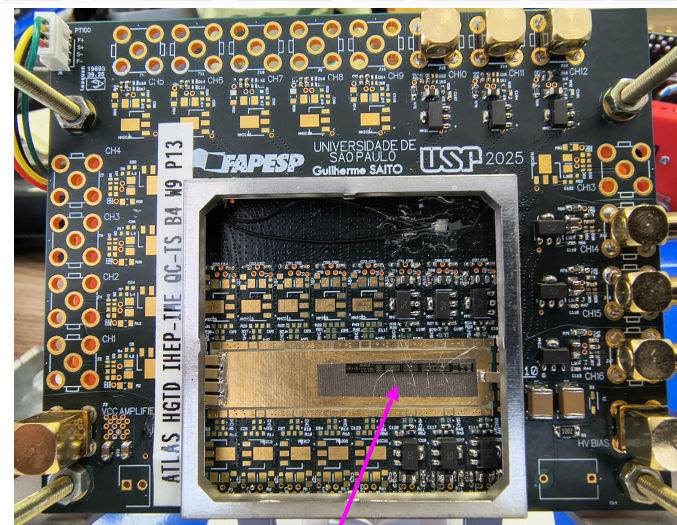
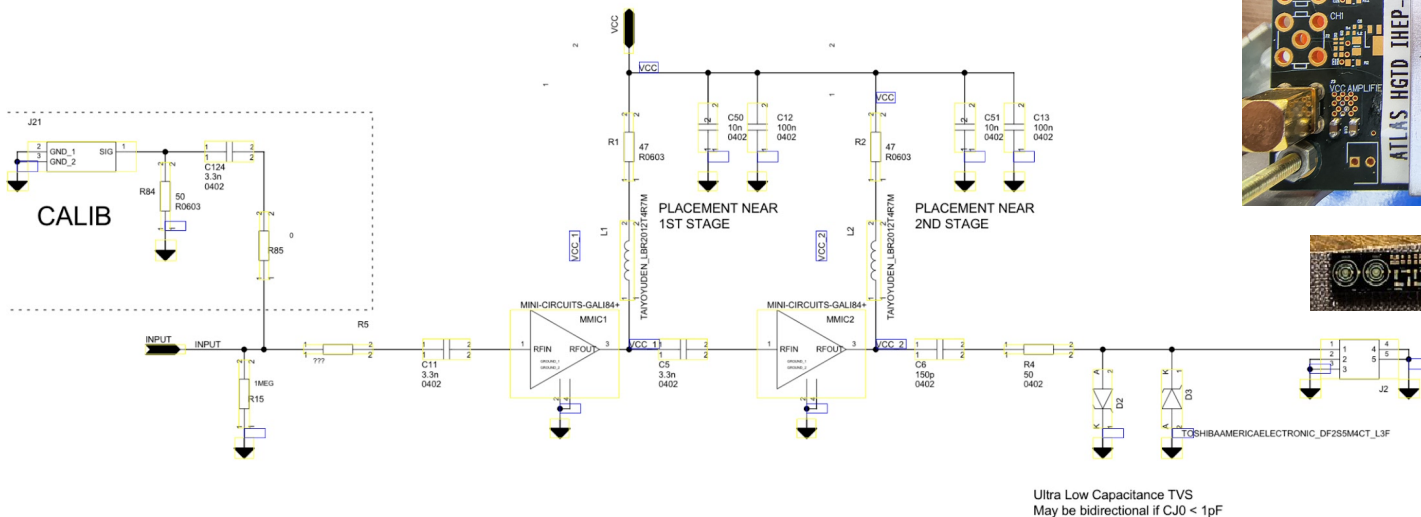
- FBK TI-LGAD sensor (V1) from RD50 production, test structures 2x1 ([Paternoster et al](#))
- 50 μm active thickness , gain ~ 20 @150V



[Paternoster et al](#)

New 16ch amplifier board

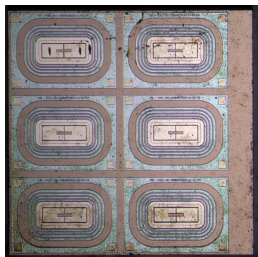
- “New” board (based on [arxiv 2504.08932v2](https://arxiv.org/abs/2504.08932v2))
- 2-stage amplifiers (MMIC Gali 52+, 2GHz , 18 dB)
- Individual charge injection
- Temperature measurement
- Removed on-board regulation due to heating ...
- Jitter < 1ps (calibration signal)



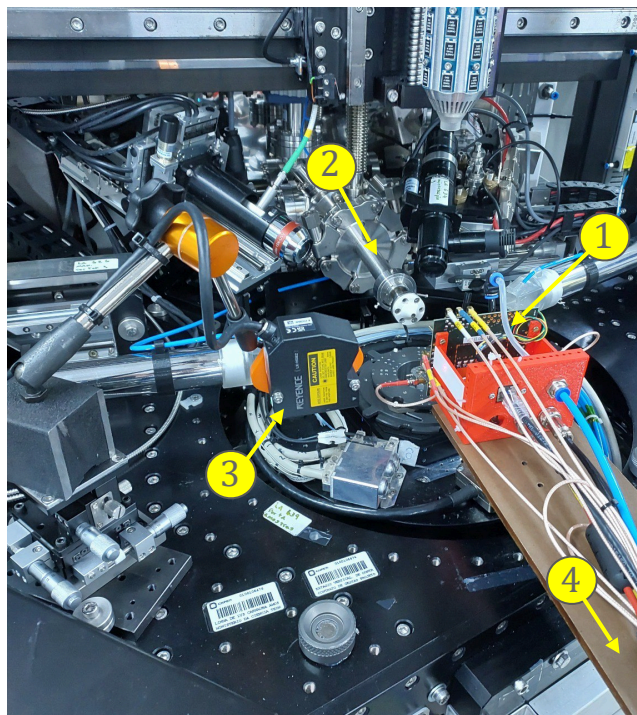
Once channel schematics (16 channels in one board)

Beam line setup

- Added a precision ($< 1 \mu\text{m}$) laser displacement sensor
- 2 oscilloscopes (up to 10 channels)
- Board is air-cooled and temperature monitored
- Beam size : $350 \mu\text{m}$ or 150 nm
- Energy and timing measurements
- Low Energy scan (2.1 keV to 6 keV)
- Measurements:
 - Position scan, timing and very high flux response



FBK TI-LGAD

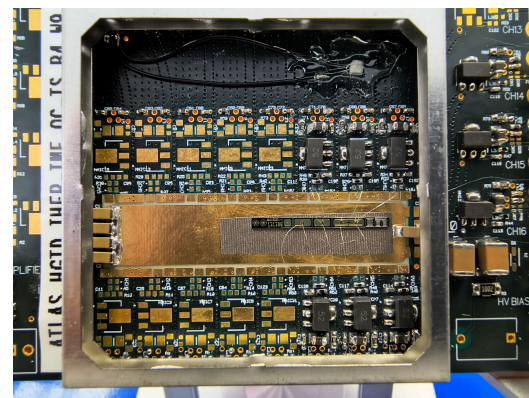
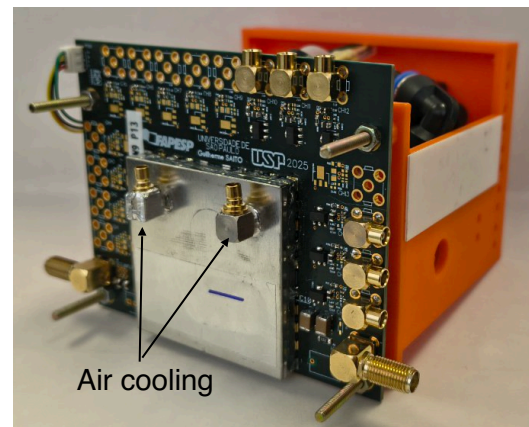


① LGAD

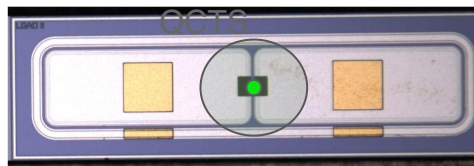
② Beam pipe

③ Laser displacement sensor

④ Linear stage

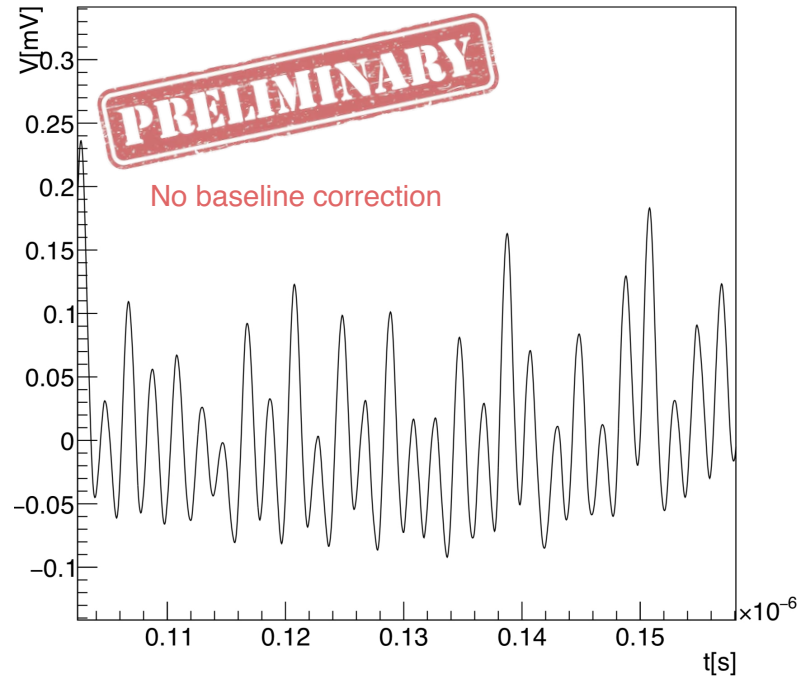


IHEP/IME
QCTS



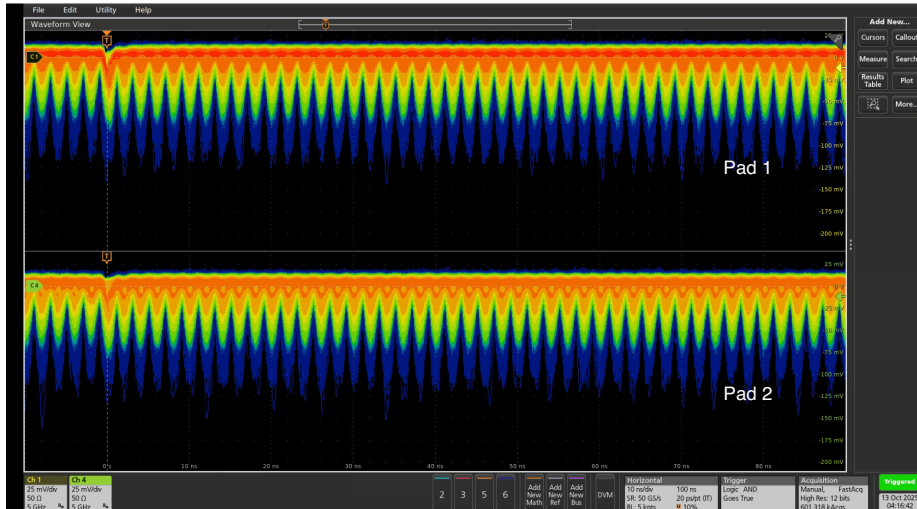
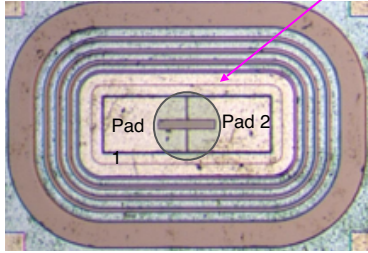
IHEP-IME LGAD response to very high flux

- An attempt to kill the sensor, but it survived ...
- Maximum flux (10^9 γ /s, $350\text{ }\mu\text{m}$ spot size) @ 6 keV
- 18uA current from sensor \Rightarrow no increase in the current in ~ 10 min operation
- 500 MHz rate, signal recorded at every bunch

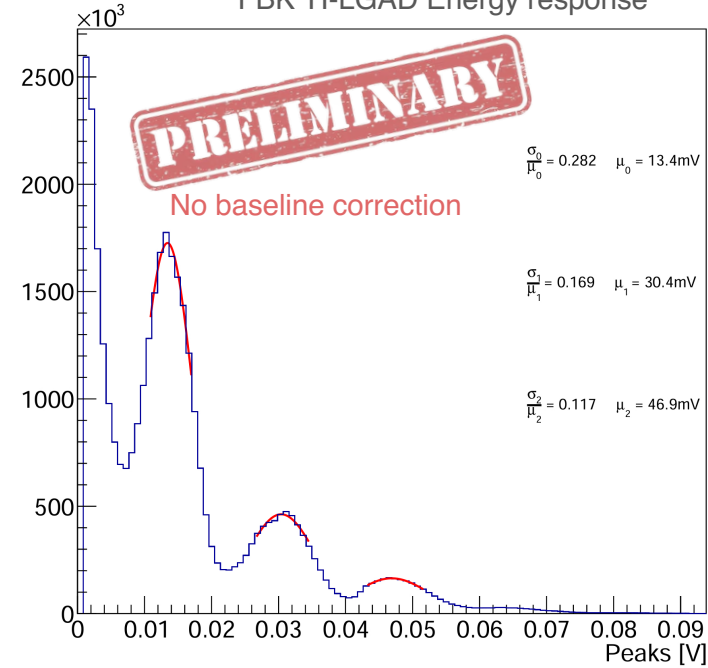


FBK TI-LGAD response

- 6 keV X-rays (350 μm spot size)



FBK TI-LGAD Energy response

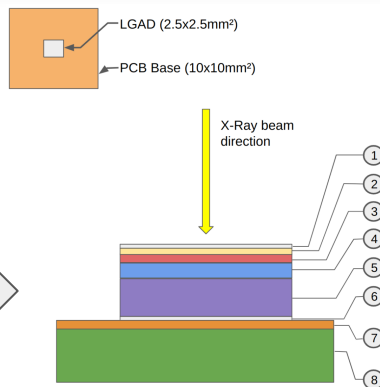


Large amount of data from both sensors (2.1 keV to 6 keV)
still being analyzed

A word on simulation

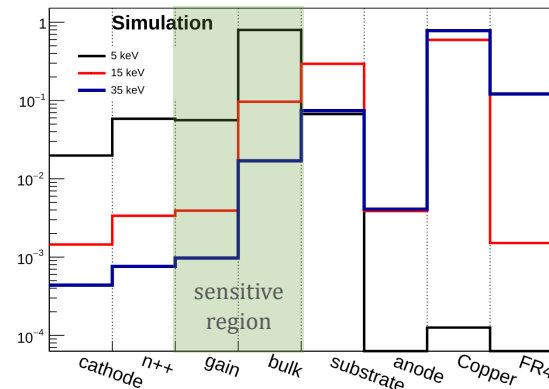
Simulations for HPK 3.1, single pad

GEANT-4 simulation of absorbed photon fraction per LGAD layer for 5, 15 and 35 keV

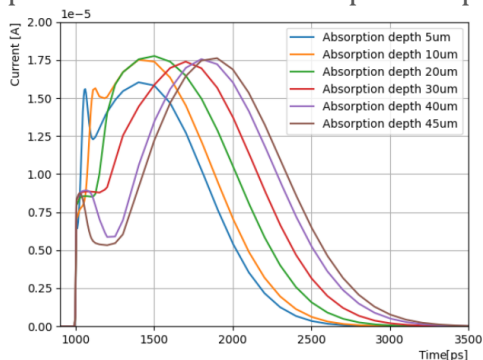


LGAD layer		Thickness (μm)
1	Al cathode Contact	0.3
2	n++	1.0
3	gain (p+)	1.0
4	bulk active	45.0
5	p++ substrate	150.0
6	Al anode contact	0.3
PCB Base layer		Thickness (μm)
7	Copper Laminate	100
8	FR4	1600

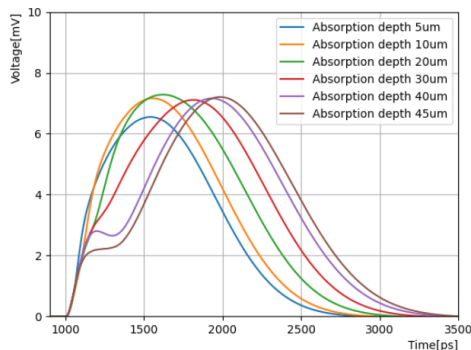
<https://iopscience.iop.org/article/10.1088/1748-0221/18/10/P10006>



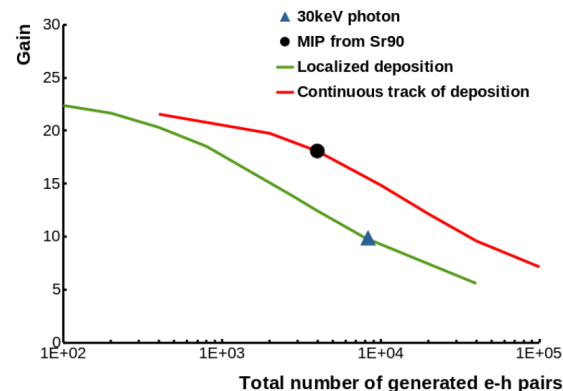
TCAD simulation of 50 μm LGAD signal response to a single 20 keV photon at different absorption depth.



(a) Current signal at the device level.



(b) Convoluted voltage signal with TIA.



Where to go from here

- None of the devices discussed here have been optimized for X-ray applications
 - However, results are very encouraging
- What we will need for photon sciences :
 - Higher energies needs thicker devices
 - Lower energies needs inverted design
 - X-rays produces localized primary charges -> Electrical field screening at different energies (see [Mazza et al](#))
 - We need to understand better signal formation for X-ray (simulations)
- Final goal : explore the response of pixel devices (AC, TI LGAD)
- However, several applications in photon sciences can use coarse (un)segmented DC-LGADS
 - Machine development studies
 - Nuclear Resonance Scattering (NRS) experiments
 - etc ...
- Faster sensors \Rightarrow faster detectors \Rightarrow faster DAQ

非常感谢！

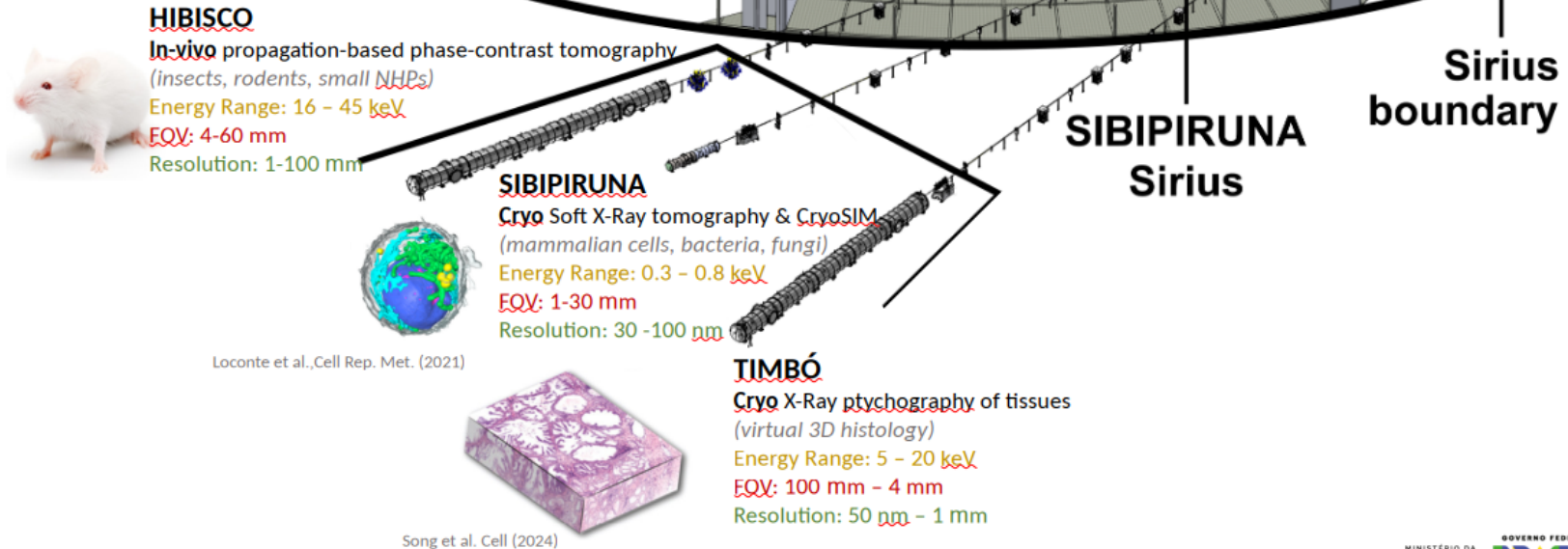


*This work was supported by
FAPESP (2022/14150-3, 2020/04867-2) and
MCTI/CNPq (INCT CERN Brasil 406672/2022-9).*



BACKUP

ORION BEAMLINES



Rascunho para o Braço extensor

